

2SC5544

Silicon NPN Epitaxial
VHF / UHF wide band amplifier

HITACHI

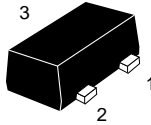
ADE-208-691 (Z)
1st. Edition
Nov. 1998

Features

- Super compact package;
(1.4 × 0.8 × 0.59mm)
- Capable low voltage operation ;
($V_{CE} = 1V$)

Outline

MFPAK



1. Emitter
2. Base
3. Collector

Note: Marking is "YZ-".

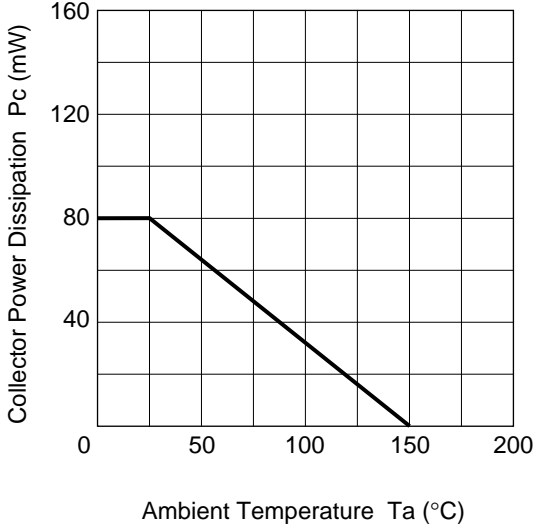
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	15	V
Collector to emitter voltage	V_{CEO}	8	V
Emitter to base voltage	V_{EBO}	1.5	V
Collector current	I_{C}	50	mA
Collector power dissipation	P_{c}	80	mW
Junction temperature	T_{j}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

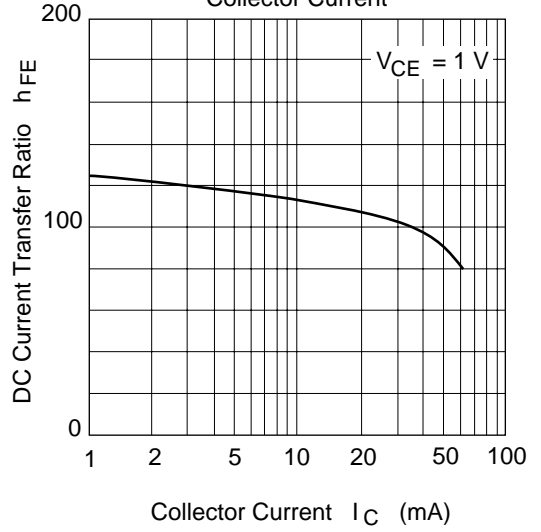
Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector to base breakdown voltage	$V_{(\text{BR})\text{CBO}}$	15	—	—	V	$I_{\text{C}} = 10\mu\text{A}$, $I_{\text{E}} = 0$
Collector cutoff current	I_{CBO}	—	—	1	μA	$V_{\text{CB}} = 12\text{V}$, $I_{\text{E}} = 0$
Collector cutoff current	I_{CEO}	—	—	1	mA	$V_{\text{CE}} = 8\text{V}$, $R_{\text{BE}} = \infty$
Emitter cutoff current	I_{EBO}	—	—	10	μA	$V_{\text{EB}} = 1.5\text{V}$, $I_{\text{C}} = 0$
DC current transfer ratio	h_{FE}	85	—	170	V	$V_{\text{CE}} = 1\text{V}$, $I_{\text{C}} = 5\text{mA}$
Collector output capacitance	C_{ob}	—	0.88	1.4	pF	$V_{\text{CB}} = 1\text{V}$, $I_{\text{E}} = 0$ $f = 1\text{MHz}$
Gain bandwidth product	f_{T}	3	6	—	GHz	$V_{\text{CE}} = 1\text{V}$, $I_{\text{C}} = 5\text{mA}$
Power gain	PG	8	11.6	—	dB	$V_{\text{CE}} = 1\text{V}$, $I_{\text{C}} = 5\text{mA}$ $f = 900\text{MHz}$
Noise figure	NF	—	1.0	2.0	dB	$V_{\text{CE}} = 1\text{V}$, $I_{\text{C}} = 5\text{mA}$ $f = 900\text{MHz}$

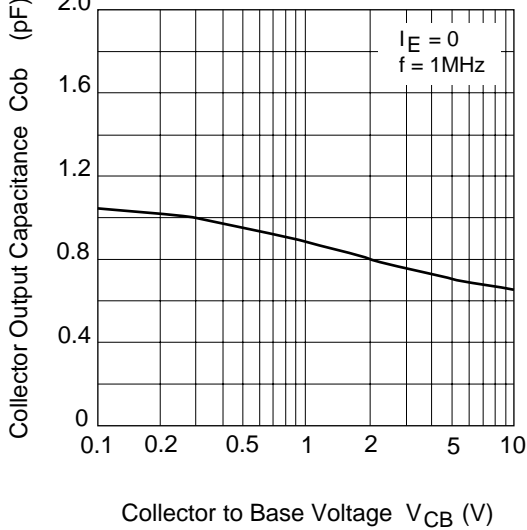
Maximum Collector Dissipation Curve



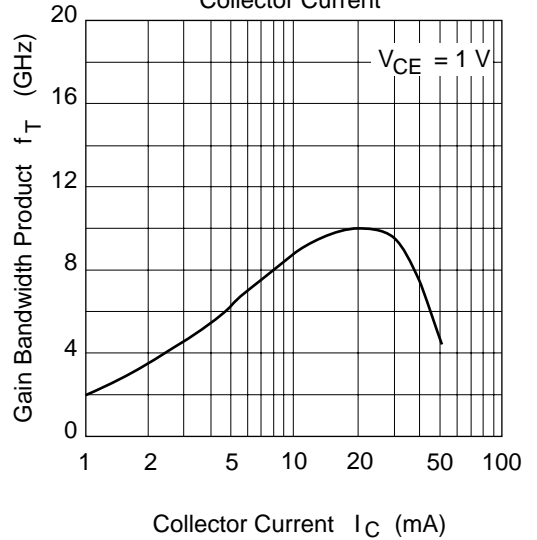
DC Current Transfer Ratio vs. Collector Current

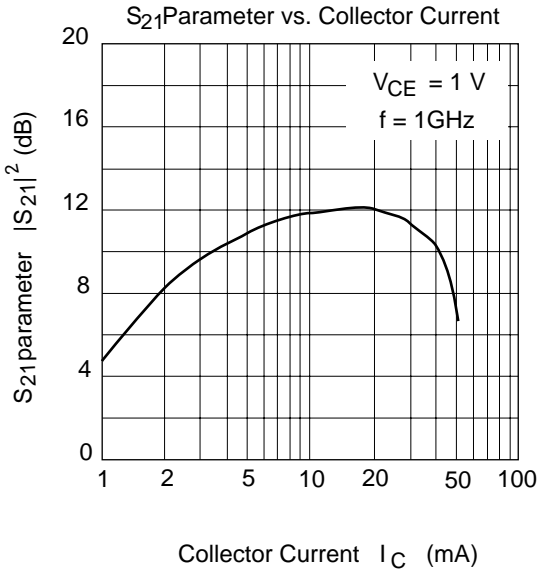
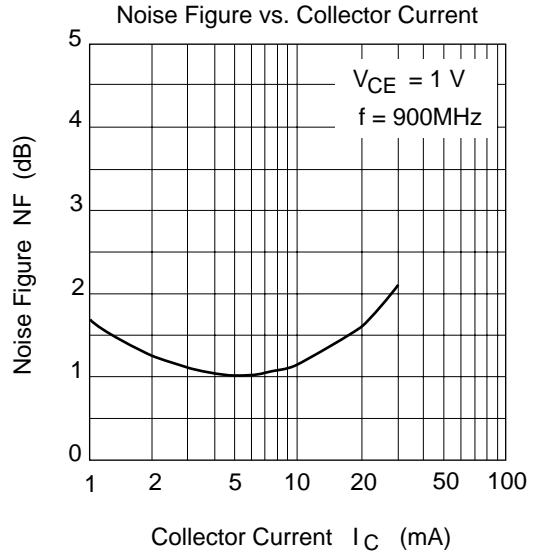
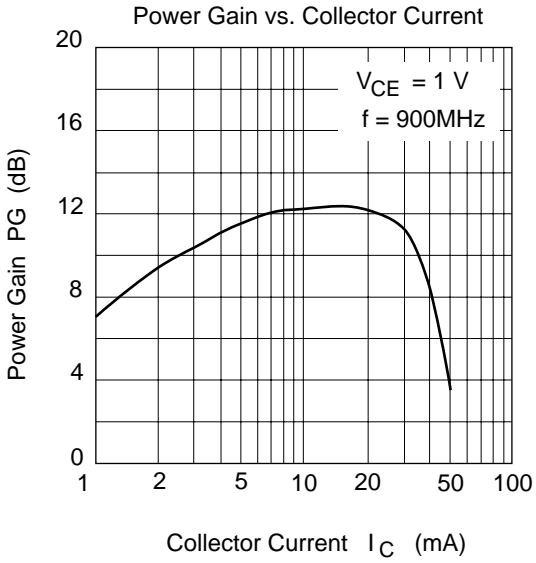


Collector Output Capacitance vs. Collector to Base Voltage

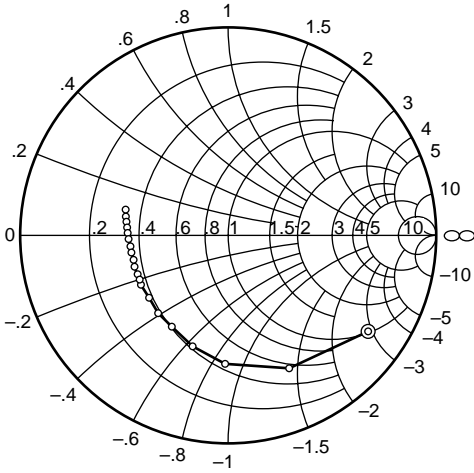


Gain Bandwidth Product vs. Collector Current





S11 Parameter vs. Frequency

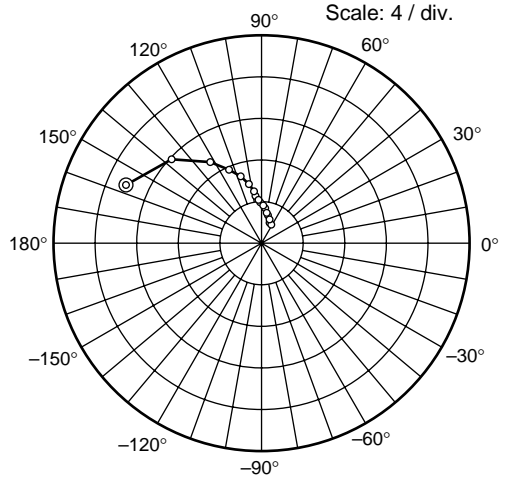


Condition : $V_{CE} = 1 V, I_C = 5mA$

100 to 2000 MHz (100 MHz step)

⊙—○

S21 Parameter vs. Frequency

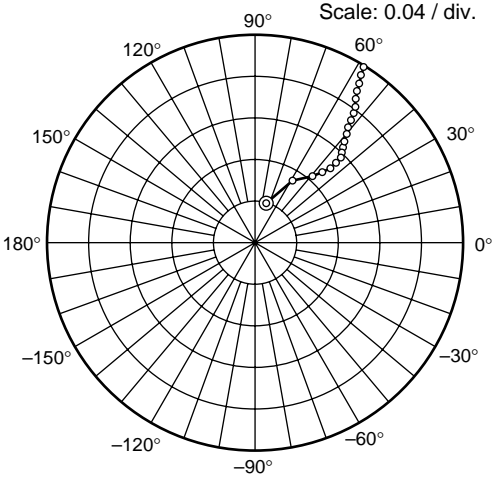


Condition : $V_{CE} = 1 V, I_C = 5mA$

100 to 2000 MHz (100 MHz step)

⊙—○

S12 Parameter vs. Frequency

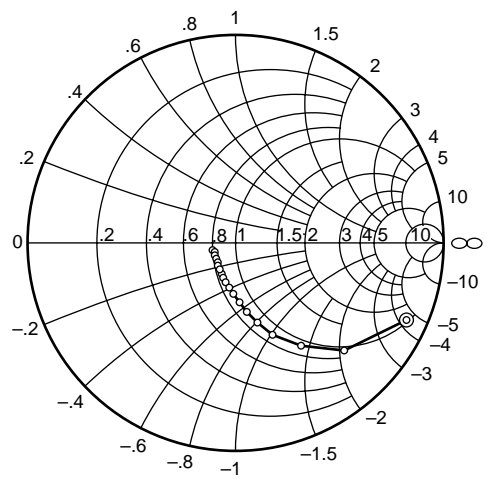


Condition : $V_{CE} = 1 V, I_C = 5mA$

100 to 2000 MHz (100 MHz step)

⊙—○

S22 Parameter vs. Frequency



Condition : $V_{CE} = 1 V, I_C = 5mA$

100 to 2000 MHz (100 MHz step)

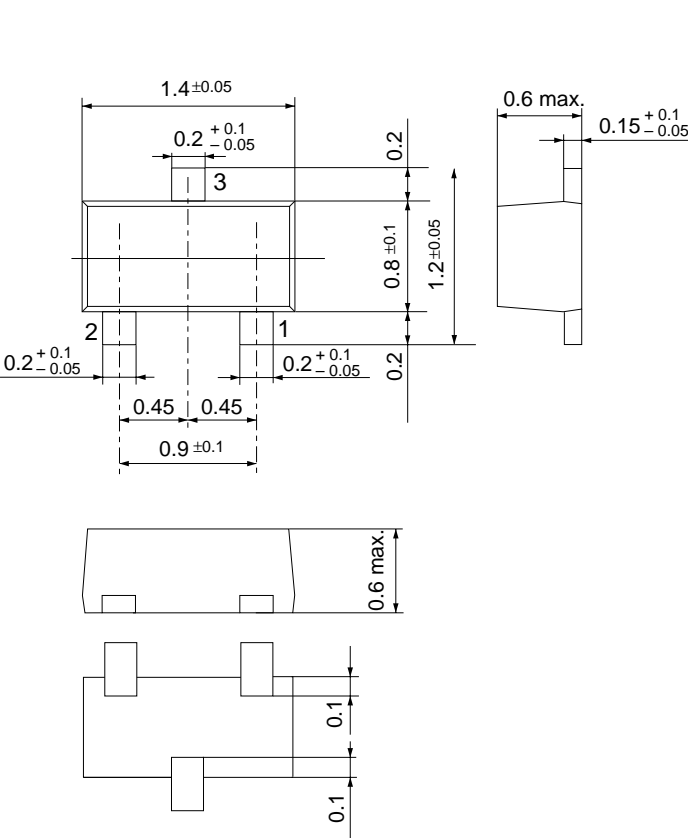
⊙—○

Sparameter ($V_{CE} = 1V$, $I_C = 5mA$, $Z_o = 50\Omega$)

f (MHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
100	0.806	-34.7	14.09	156.3	0.0395	71.3	0.905	-24.2
200	0.706	-66.0	11.64	136.7	0.0691	57.5	0.739	-44.3
300	0.617	-90.3	9.35	122.8	0.0860	49.4	0.586	-58.1
400	0.562	-108.0	7.66	113.8	0.0965	45.8	0.474	-67.6
500	0.527	-121.9	6.40	106.7	0.104	44.3	0.392	-74.9
600	0.500	-133.0	5.47	101.7	0.110	43.9	0.331	-81.1
700	0.487	-142.3	4.78	97.0	0.115	44.5	0.284	-86.2
800	0.480	-149.3	4.24	93.7	0.121	45.4	0.247	-91.2
900	0.481	-155.4	3.81	90.5	0.127	46.3	0.217	-96.2
1000	0.472	-161.4	3.46	87.8	0.132	47.7	0.193	-100.8
1100	0.473	-166.6	3.18	85.1	0.138	48.9	0.174	-106.2
1200	0.475	-170.5	2.94	82.8	0.144	50.3	0.157	-111.2
1300	0.478	-174.4	2.73	80.6	0.150	51.7	0.145	-115.7
1400	0.482	-178.1	2.56	78.6	0.157	52.8	0.135	-122.6
1500	0.488	178.4	2.41	76.6	0.163	53.7	0.125	-128.1
1600	0.494	175.9	2.28	74.9	0.171	55.0	0.119	-134.2
1700	0.503	172.5	2.16	73.2	0.177	55.9	0.116	-140.3
1800	0.509	169.9	2.06	71.4	0.185	56.9	0.114	-147.1
1900	0.515	167.7	1.97	69.8	0.191	57.5	0.114	-153.3
2000	0.520	165.8	1.89	68.4	0.199	58.3	0.115	-159.4

Package Dimensions

Unit: mm



Hitachi Code	MFPK
EIAJ	—
JEDEC	—

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